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G09G 3/36

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(43)

2003-0041787
2003 05 27

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(22) 2002 11 18

(30) JP-P-2001-00353282 2001 11 19 (JP)

(71) 211-8668 가 가 가 1753

(72) 가 가 4-12-12 가 ()

(74)

:

(54)

3-N) (100)가 (100) (3-1)
(35) (35) (DIN) 가
(21) (21) (PS)
(35) (21)

1

1

2 AB

3 B

4 B

5

6

7 B

8 6

9

10

11

12

1 : 2 :

3-1 3-N : 4-1 :

4-2 : 31 :

32, 33, 1133 : D/A 35, 635 : B

100 : 500 :

501 : 502 : TFT

503 : 504 :

505 : 506 :

507 : TFT

, EL(Electro - Luminescent) (source driv
er)

, TFT(Thin Film Transistor)

가

(,),

. TFT

((row))

(,)

가

10 (1000)

4-242788

가 1000 (1000)

(DIN)

(DIN)

(1003-1 (1003-1

1003-N) 1003-N)

(VR1 VR64) (R), (G), (B) 64- 65

(VR1 VR64)

(4-1 4-2)

(DIN)

(1003

-1 1003-N) (DL) (32)

(31),

(D/A) 가 (32), (31)

(1034) (31)

(31) D/

A (1034)

. D/A . D/A

(32)

(D/A) AB

(VR1 VR64) (1034)

. AB (voltag

e follower) PS-N)

. AB

(1034) (VR1 VR64)

. AB (1003-1 1003-N)

(PS-1

(PS-1 PS-N)

(PS-1 PS-N) B (1034)

(PS-1 PS-N)

A

, AB (1034) (VR1 VR64)

B (1034)

(PS-1 PS-N)가 (PS-1 PS-N)

, A

VR64) 가

가

, AB

AB (1034) (PS-1 PS-N)

(VR1

11 (1100)

03-N) AB

10-326084 (1034)가 (VR1 VR64)

가 1100

(1100) (1000)

(1103-1 1103-N)

11

가 (1102)가

.

(1100)

(1)

(1103-1 (1000)

(1000)

PS-N) (1100)

.

(VR1 VR64) (1102) 가

(1000) AB

(1034)

(PS-1

가

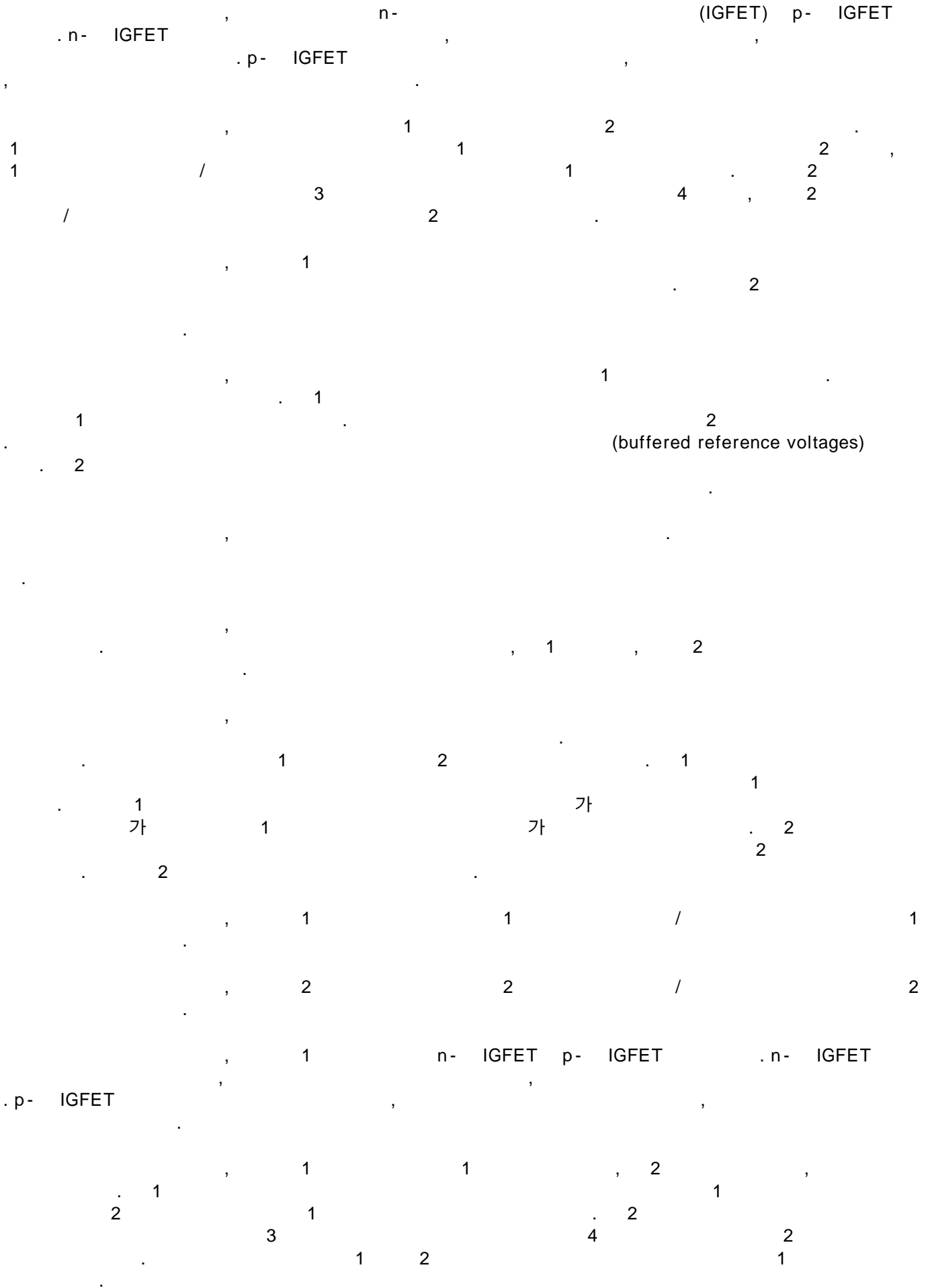
(1000 1100)

AB

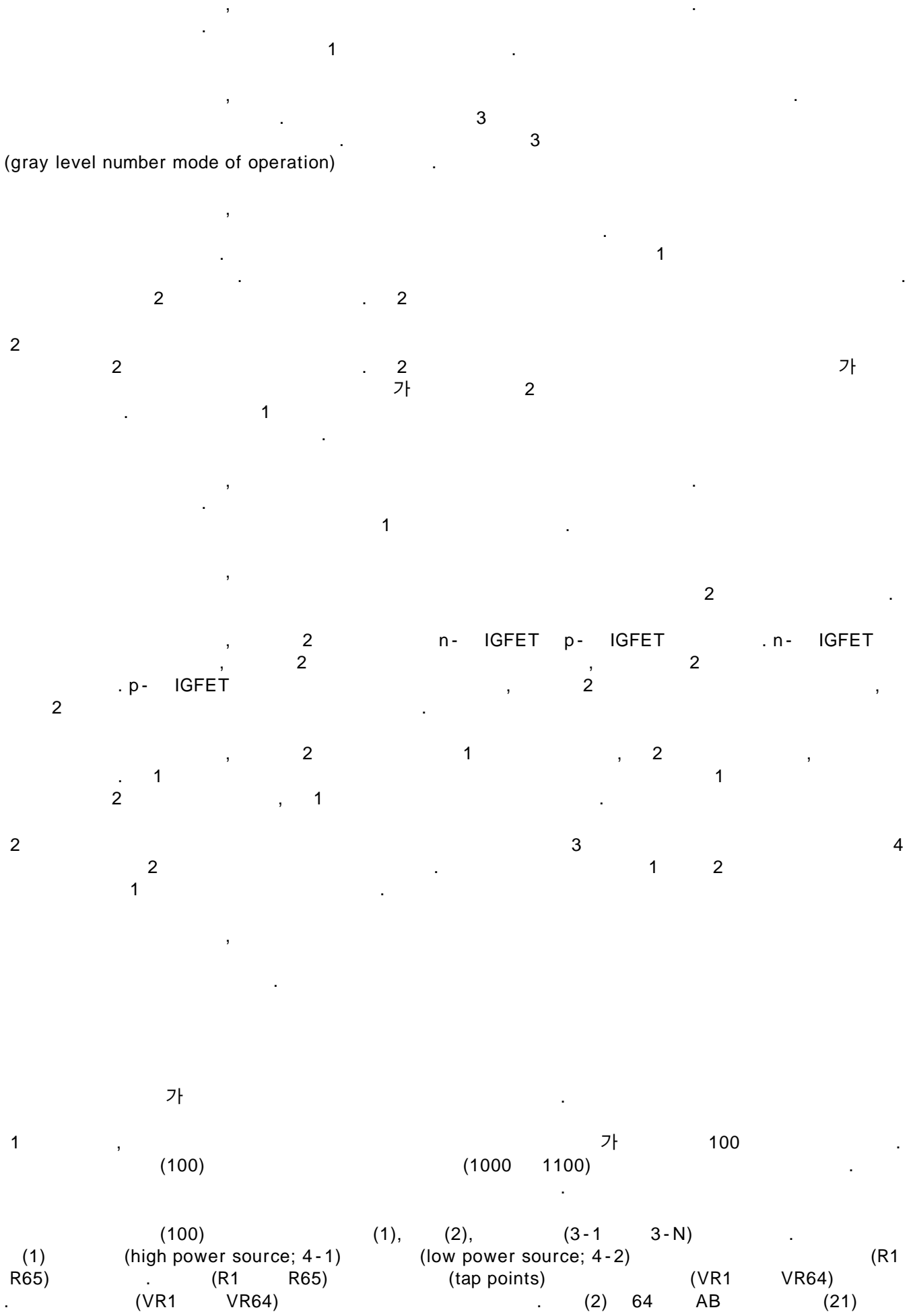
가

가

가 11-305744
 가 1200
 12
 (1200) 11-305744 (DIN) (V1 VM) (1230)
 (1230) (DIN) (V1 VM) (1230) () ()
 1230) (1000 1100) D/A (32 1133) 가 , ()
 (1200) (OUT) (1234)
 (1234)
 (1200) (CONT)가 () 가 , ()
 1234) (OUT) (CONT)가 () 가 , ()
 1234) (1234)
 0
 (1200) (1230) (OUT) (1236)
 (1236) (1238) (TG1) (CONT)가 ,
 (1236) (TG1) (1230) (OUT) (1234)
 (V1 VM) (CONT)가 (1230) (TG1) (OUT)
 (DIN)가 (CONT) (OUT) (CO
 (1234) (V1 VM) (OUT) (CO
 NT) (1230) (V1 VM) (1234)가 (1200)
 (1200) (CONT)가 (1234) (1236)
 (CONT) (CONT)
 0.2V /
 가 (CONT) 가 (CONT)가 /
 가 (CONT)가 (1234) 가
 (CONT) (1200) (C
 ONT)
 가
 (35) 가
 1 1



(gray level number mode of operation)



AB (21) (VR1 VR64)
(VA1 VA64), (VA1 VA64) AB (21)

(3-1 3-N) (DIN), (VR1 VR64),
(DL) (PS-1 PS-N)
(VA1 VA64), (3-1 3-N) (31), (D/A) (32 33), B (35)
(31) (31) (DIN) (DL) (SS) D/A (32) (32)
33) (35) D/A (32) B (SS) (VR1 VR64) B (32)
(35) (35) (33) (SS) (35) (PS-1 PS-N) (VA1 VR4) (PS)
-1 PS-N)

(dead zone) B (35)가 B
(35) AB (10 AB / AB (21)) B
(35) AB (1034) (PS)

AB (21) B (35) 가 2 3
2 , AB 가 200 AB (200)
가 (100) AB 11-239303 (21) (16) AB (200) 1 (200)

AB (200) (201 202) (203)
(K1) AB (200) (K1), (K2), (K3) (K2)
(A5) (A3 A4) (AC ACB) AB
(200) (AC) (ACB) (200)가 , AB ()
200)가 (AC) (ACB) (ACB)

2 AB (200) (203)
(M66e) (M65e)
(M66e) (M65e) (203)
가 (M66e) (M65e) (VDD) (VSS)
(203)가 10 AB (1034)
(M66e) (M65e)

B 가 3 B 3 B
가 300 (300) 1 (100)
B (35) B (300) n- IGFET(insulated gate fie
ld effect transistor; 303) p- IGFET(304) n- IGFET(303)
(VDD) (302) (301) p- IG
FET(304) (VSS) (302) (301) (301)

n- IGFET(303) p- IGFET(304) n- MOSFET p- MOSFET
n- IGFET(303)가 (VDD) p- IGFET(304)가 (VSS) B
(300) () IGFET)

B (300) (301) (302) n- IGFET(303)
(301) n- IGFET(303) (302)
(301) (302) p- IGFET(304) ,
(301) p- IGFET(304) (302)

(301) (302) .

) , (301) (302) n- IGFET(303) (302)

) p- IGFET(304) , B (300) p- IGFET(304)

4) GFET(303) 0.4V p- IGFET(304) B (300) , n- IGFET(303) p- IGFET(304)

, 2.1V 2.9V B (300)가 -0.4V (302) 2.5V

n- IGFET(303) p- IGFET(304) 가 , n- IGFET(303) p- IGFET(304)

가 FET(304) (VDD) (VSS) n- IGFET(303) p- IG

B (300) 가 n- IGFET(303) p- IGFET(304)

4 , B 가 400 . B

(404 406) (100) B (35) . B (400)

, (404 406) (404 406) , ,

(404 406) , ,

T(M1) (404) p- IGFET(M1 M2), n- IGFET(M3 M4) (CS1) . p- IGFE

, p- IGFET(2) (VDD) , p- IGFET(M9) n- IGFET(M3) (VDD)

, p- IGFET(M1) n- IGFET(M4) . p- IGFET(M2)

. n- IGFET(M3) (401) n- IGFET(M4) (CS1) 1

S1) (VSS) 2 . n- IGFET(M4) (402) . (C

ror load)(p- IGFET(M1 M2)) (n- IGFET(M3 M4)) (404) (current mir

T(M5) (406) n- IGFET(M5 M6), p- IGFET(M7 M8) (CS2) . n- IGFE

, n- IGFET(M6) (VSS) , n- IGFET(M10) p- IGFET(M7) (VSS)

, n- IGFET(M5) p- IGFET(M8) . n- IGFET(M6)

. p- IGFET(M7) (401) p- IGFET(M8) (CS2) 1

(CS2) (VDD) 2 . (406) (n- I

GFET(M5 M6)) (p- IGFET(M7 M8)) .

(408) p- IGFET(M9) n- IGFET(M10) . p- IGFET(M9) (VDD)

, (402) (404) p- IFGET(M1) n- IGFET(M3)

, (406) p- IFGET(M7) n- IGFET(M5) . n- IGFET(M10) (VSS) , (402)

(404) , (401) (402)

(408) p- IGFET(M9) . p- IGFET(M1) , p- IGFET(M2) p- IGFET(

, (401) (402) p- IGFET(M1)

(408) p- IGFET(M9) (VDD) p- IGFET(M9) , p- IGFET(M1 M2) ()

, (402) p- IGFET(M9) , n- IGFET(M3 M4) (401)

, (404) , (401) (402)

, p- IGFET(M9) (401) (402)
 , p- IGFET(M9)

(40) (401) (402)
 (408) n- IGFET(M10) , n- IGFET(M5) n-
 IGFET(M6) . n- IGFET(M6) n- IGFET(M6)
 (401) (402) n- IGFET(
 M5) (VSS) n- IGFET(M10)
 (408) n- IGFET(M10) , n- IGFET(M5 M6) ((4
)) n- IGFET(M10) , p- IGFET(M7 M8) (4
 01) (402)

(406) (401) (402)
 , n- IGFET(M10) (401) (402)
 , n- IGFET(M10)

(400) (401) 가 (402)
 (404) (402) (406)
 , B (400) , p- IGFET(M9) n- IGFET(
 M10) 가 (402)

(404) 0.2V (406) -0.2V ,
 (402) 2V , (402)가 1.8V 2.2V (408)
 (402) 0 (404 406)

(401) (401) , p- IGFET(M9) n- IGFET(M10)
 (402) (402) 가
 (404 406) 가 0V 가
 (402) , (408) 가 (401) 가
 , 0.2V 0.5V 가
 1 (100)

(3-1 3-N) , B (35) D/A (32)
 (PS-1 PS-N) . B (35)
 가 (PS-1 PS-N) , B (35) D/A (32)
 (PS-1 PS-N) (2) AB (21) . AB (21)
 (3-1 3-N) D/A (33) (VA1 VA64) . AB (2) (D/A
 (33)) (PS-1 PS-N) . AB (21)

(33) AB (100) (PS-1 PS-N) (D/A
 () (221) B (35)가 (1000 1100) 가
 , B (35) 0 () 가
 (1000) AB (1034) 가
 , B (35) (PS-1 PS-N) . AB
 (21) 가 (가) (PS-1 PS-N)
 . AB (21)가 가
 , AB (21) (1100) (1102) AB
 (100) (2)

(35) (1100) (1000 1100) (1102) AB (1034) AB
 (1000 1100) (1000 1100) (1034) AB
 가 가 , 가 가 (100) , 1 , (P
 S-1 PS-N) 가 가
 B (35)가 , AB (21) B
 (35) B (35)
 , 가 5 9 . 1 가 ()
 , TFT
 (PS)
 (PS)
 5 , 가 500 .
 TFT (501) (500) (503) (501), TFT (502), (503)
 (501) (502) (503) (LSI) TFT (502)
 (PS1 PSN) (503) (501) (PS-1 PS-N) TFT (502)
 TFT (502) (504) (504) (PS1 PSN) (501) (501)
 (504) N×M (501) (505) N
) (504) K M (PSK)(K 1 N
 (504) (505) M (505)
 (505) (PS) M
 (505) TFT (502) (TFT; 507) ()
) (503) (506) , TFT(507) TFT(507)
 5 , TFT(507) (507) N×M (505) TFT(507)
 (506) TFT(507) n- () (506) (506) (506)
 (508) TFT(507)가 (506) (505) (508)
 (508) TFT(507)가 (506) (506) TFT(507)
 (504) () (501))
 , (PS) 가 ,
 , 가
 , 가 , ,
 가 가 , ,
 가 가 6 .
 6 , 가 600 .
 (600) (100) (600) 4 ,
 64 260,000 , 16 , 4,
 096 , 8 512 , 2

8

1 (100) , 64 AB (21) 64
 (VA1 VA64) , 16 AB (602)가 (600)
 , 16 16 AB (602)가 (600)가
 , 16 (VR1 VR64) 16
 16 AB (602) , AB (602) (PA1 PA3) /
 , AB (602) (602) (602) 0
 16 AB (602) , (PA1) 2- 2 AB
 (602) (PA2) 8- 6 AB
 (602) 2- , 2 AB
 (200)가 AB (602) , (PA1 PA3) (AC)
 (PA1 PA3) (ACB)

5) D/A (32) (600) (603-1 603-N) , AB (634) B (63
 (AS1) AB (PS-1 PS-N) , B (635)
 (635 634) (634) (AS2) (AS1 AS2)
 AB (200) AB (634) , (635 634) 2
 (AS2) (ACB) (AS2) (AC)

, B (635) , (AS1) , 1
 B (35) 가 .

(AS1)가 , B (635) (635) 가 .
 , B (635) 0 .

7 , B 가 700 . B
 (700) (600) B (635) . B (700) 4
 B (400)
 B (700) (704 706) (708)

(CS1) n- IGFET(M14)가 n- IGFET(M11 M13)가
 (704) (404) . n- IGFET(M14) n- IGFET(M3 M4)
 , (VSS) , n- IGFET(M11 M12)
 . n- IGFET(M11) (NBIAS) , (AS1)
 n- IGFET(M12) n- IGFET(M12)
 . n- IGFET(M13) (VSS) (AS1B)
 p- IGFET(M1 M2) (VSS) n- IGFET(M4) p- IGFET(M2)

(CS2) p- IGFET(M19)가 p- IGFET(M16 M18)가
 (706) (406) . p- IGFET(M19) p- IGFET(M7 M8)
 , (VDD) , p- IGFET(M16 M17)
 . p- IGFET(M16) (PBIAS) , (AS1B)
 . p- IGFET(M17) p- IGFET(M18 M19) p- IGFET(M17)
 . p- IGFET(M18) (VDD) (AS1)
 n- IGFET(M5 M6) (VDD) p- IGFET(M8) n- IGFET(M6)

p- IGFET(M15) n- IGFET(M20)가 (708) (408)
 p- IGFET(M15) (VDD) , p- IGFET(M9) p- IGFET(M1) n-
 IGFET(M3) (AS1) , n- IGFET(M10) n- IGFET(M5) p- IGF
 IGFET(M20) (VSS) , n- IGFET(M10) n- IGFET(M5) p- IGF
 ET(M7) (AS1B)

(AS1)가 (AS1B)가 B (700) B (

400)

(AS1)가 IGFET(M11) , p- IGFET(M17) (AS1B)가 IGFET(M16) , n- IGFET(M12) , n- IG
n- IGFET(M13 M14) IGFET(M17)가 IGFET(M17)가 IGFET(M12)가 IGFET(M18 M19)
- IGFET(M18 M19) , n- IGFET(M13 M14) , p- IGFET(M18 M19) , p
(704 406) 가

(VDD) (AS1)가 IGFET(M15) p- IGFET(M9)
(VSS) (AS1B)가 IGFET(M20) n- IGFET(M10)
(702) (701) , p- IGFET(M9) n- IGFET(M10)
가 0 (708)

6 (600)

, 260,000

260,000 (AS1, PA1, PA2, PA3) (AS2) (A
(603-1 603-N) , AB (634) B (635) ,
S2) (602) (PA1 PA3) , AB (602) , 16
AB (AB (602)) , AB (602)
0 . AB (602) , AB (602)
1 VR64) (PD) D/A (32) (31) 6- (1) (PD) (33) (SS)
64- B (635) , D/A (32) (VR

(600) 가 AB (600)
(1000) 가 (1000)

, 4,096

4,096 (AS1) (AS2) (AS2)가 (635)
(603-1 603-N) , B (634) (AS1) AB (634) (AS2)가 (635)
634) 가 , B (634) 가 , 4,096 (PA1 P
A3) (31) , 6 (PD) (602) , 4,096 (32 33)
, (1) (1) (PD) , 4 D/A (602) (32 33)
(PS-1 PS-N) (602) 16-
4,096 , AB (634) 0
, B (635) , 260,000

512

(PA1 PA2)가 (PA3)가 512 4,096
. 16 AB (102) , 8-
8 AB (602) , 8 AB (602)
(31) , 6- (PD) , 3 D/A (32 33)
, (1) (1) (602) 8-
(PS-1 PS-N) (602) 0
12 , B (635) AB (634) 0
, 4,096 (602) 8

, 8
(PA1)가 .16 AB (602) (PA2 PA3)가 8 512 (602)
(31) 6- (1) (PD) , 1 D/A (32 33) ,
(635) , AB (634) (PS-1 PS-N) (602) 0 2 , B , 51
B (635)가 , AB (634) B
(635)가 , (603-1 603-N) (PS-1 PS-N) B
가 . B (PS-1 PS-N) , B 가 가 ,
D AB . AB , 가 가 가 , B A/D , A/
, AB 가 , AB 가 , 가 ,
, AB 가 , AB 가 ,
, 가 가 AB , B
(600) , 가 가 B , 가 , 가 AB
(602)) , 가 , B 가 , AB (AB (600)
8 , D/A , AB 6 (600) 가 B 8
(PS) (PS)가
9 , 가 , 9 260,000 , 4,096 , 512
1), , 8 (1100)(2) (600)(), 9 (1000)(,
(N) 24 (M) 22 가 ,
, 260,000 가 1 2 1 (600) AB
, 1 2 (600) , 512 4,096
가 B (600)
가 (600) , TFT , TFT ,
EL , EL TFFT , (brightness) ,
(5 TFFT (500) (505)

) EL 7 2001-0
83924

, 5 , 가 , 가 , 가 ,
, , 가 , 가 ,
, , 가 .

가 , 가 , 가
, , 가
, 가 .

, 가 .

가 , 가 , 가 ,

(57)

1. 1 1 ;

1 2. ,
,
n- (IGFET);
p- IGFET

1 3. ,
,

/ 1 1 1 2 , 1

/ 3 2 2 4 , 2

3 4.

, .

1

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2

1 5.

,

;

1

1

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,

(buffered reference voltages)

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2

5 6.

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1 7.

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1

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2

8.

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1

1 가 1 가 가 1 ;

2

2

9.

8 , 1 1 / 1

10.

8 , 2 2 / 2

11.

8 , 1 , n- , 1 (IGFET); , 1 p- IGFET , 1 , 1

12.

8 , 1 , 1 1 ; 2 2 3 ; 4 1 2 , 1

13.

8 , , 1

14.

8 , ;

3

,

3

(gray level number mode of operation)

15.

,

1

;

,

,

2

2

가

2

가

가

2

,

1

16.

15

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,

2

1

17.

16

,

2

18.

15

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2

,

n-

2

(IGFET);

2

p-

IGFET

2

2

19.

15

,

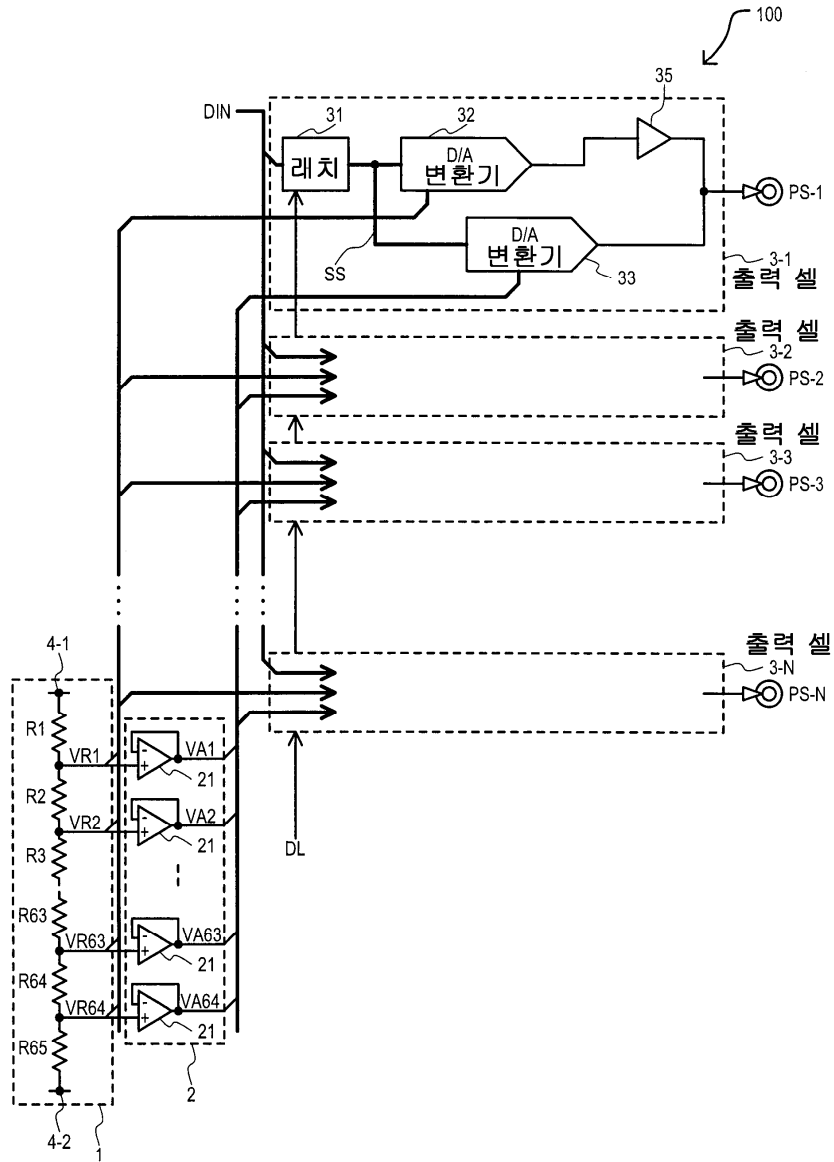
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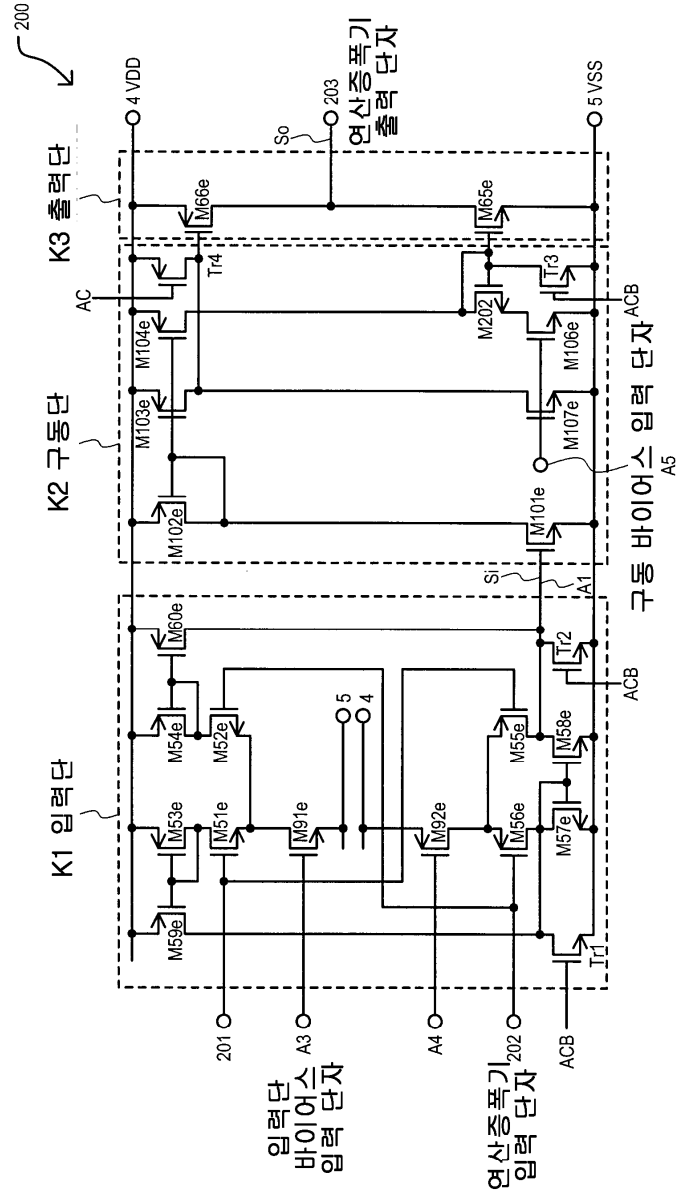
1 1 ; 2 1
2 3 ; 4 2

1 2 2 .

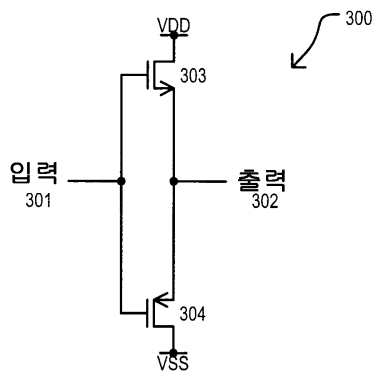
15 20. ,

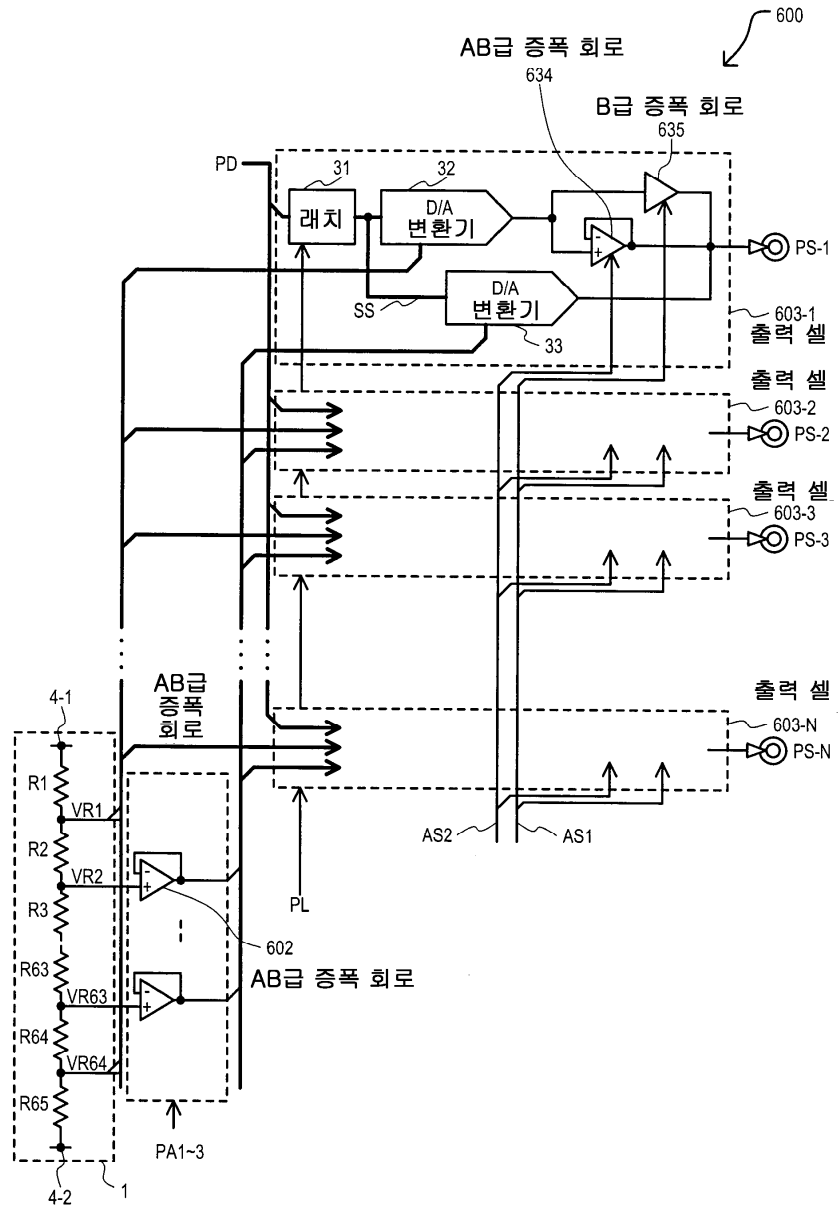


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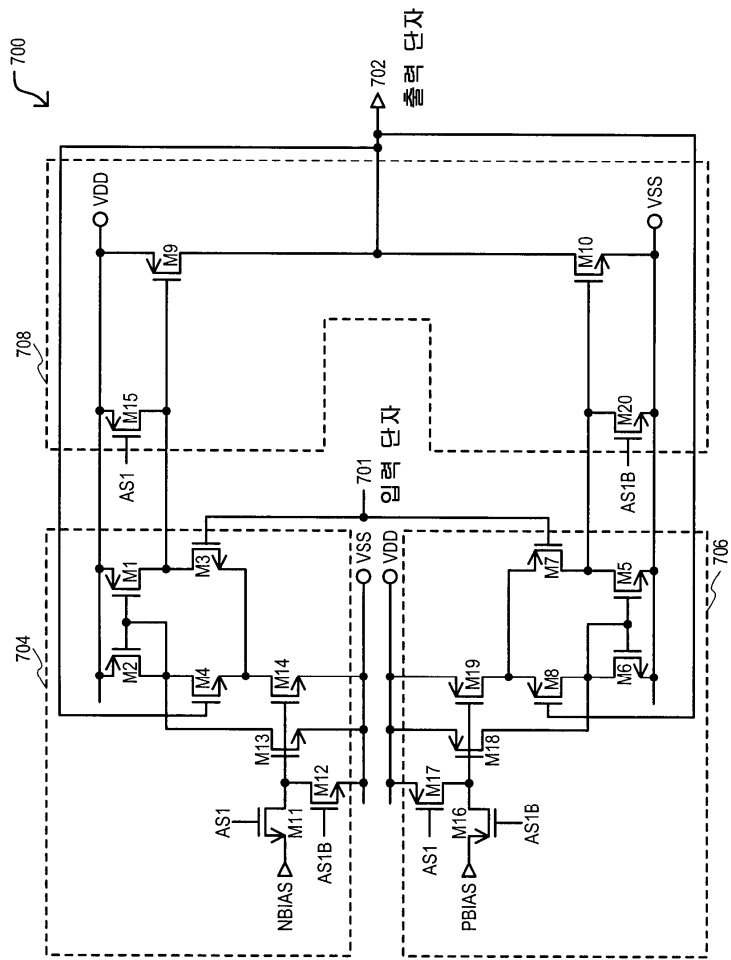


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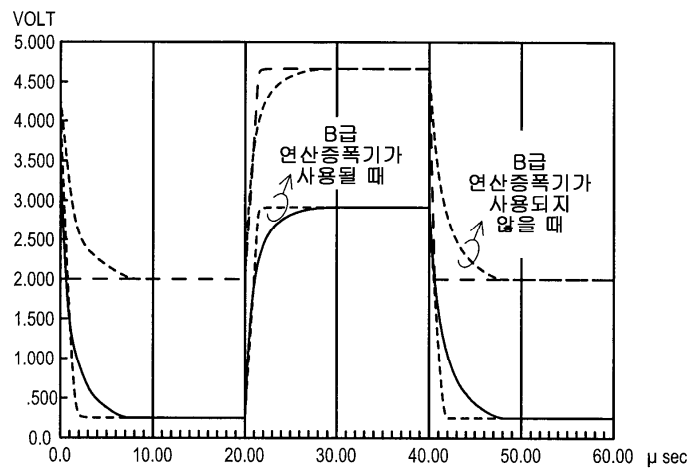




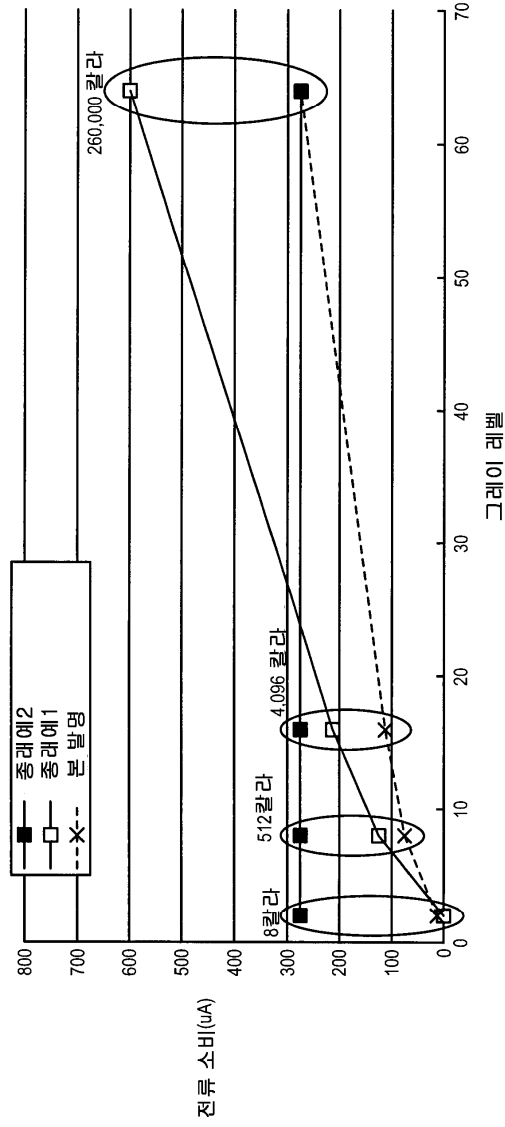
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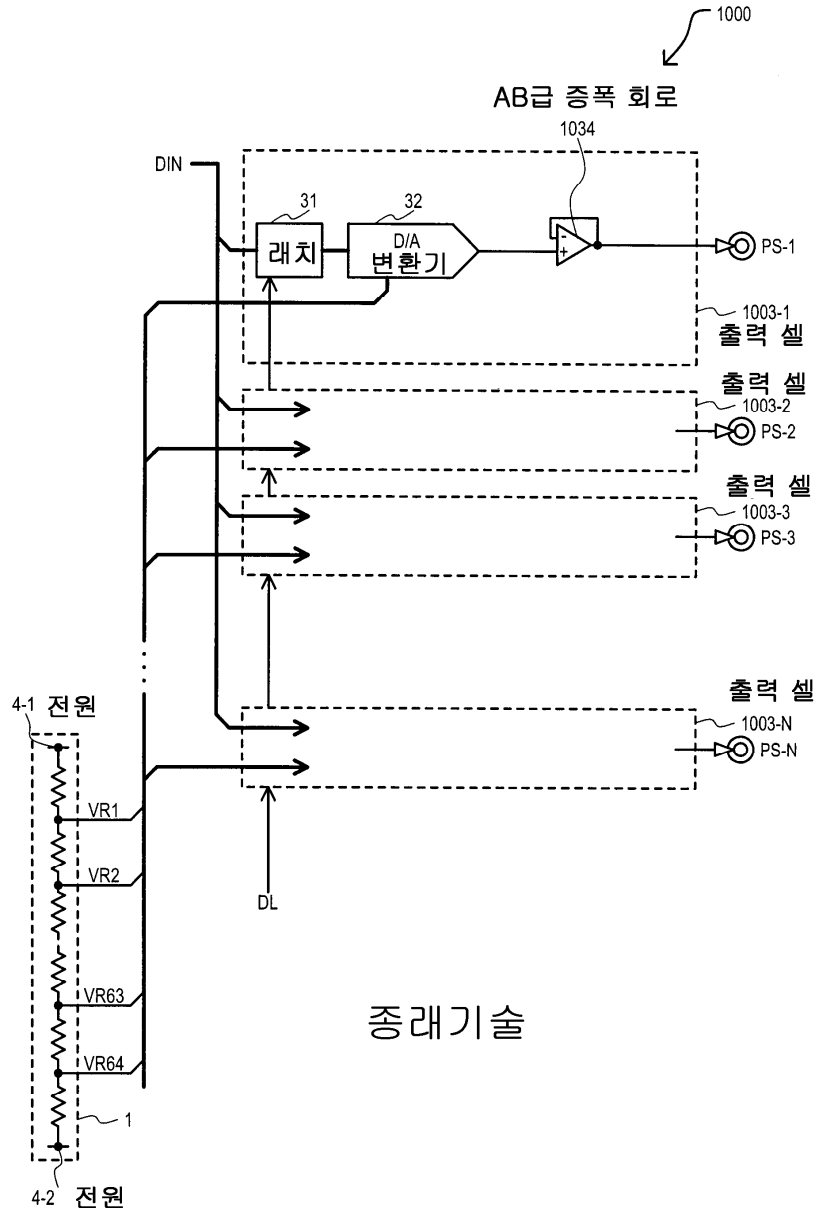


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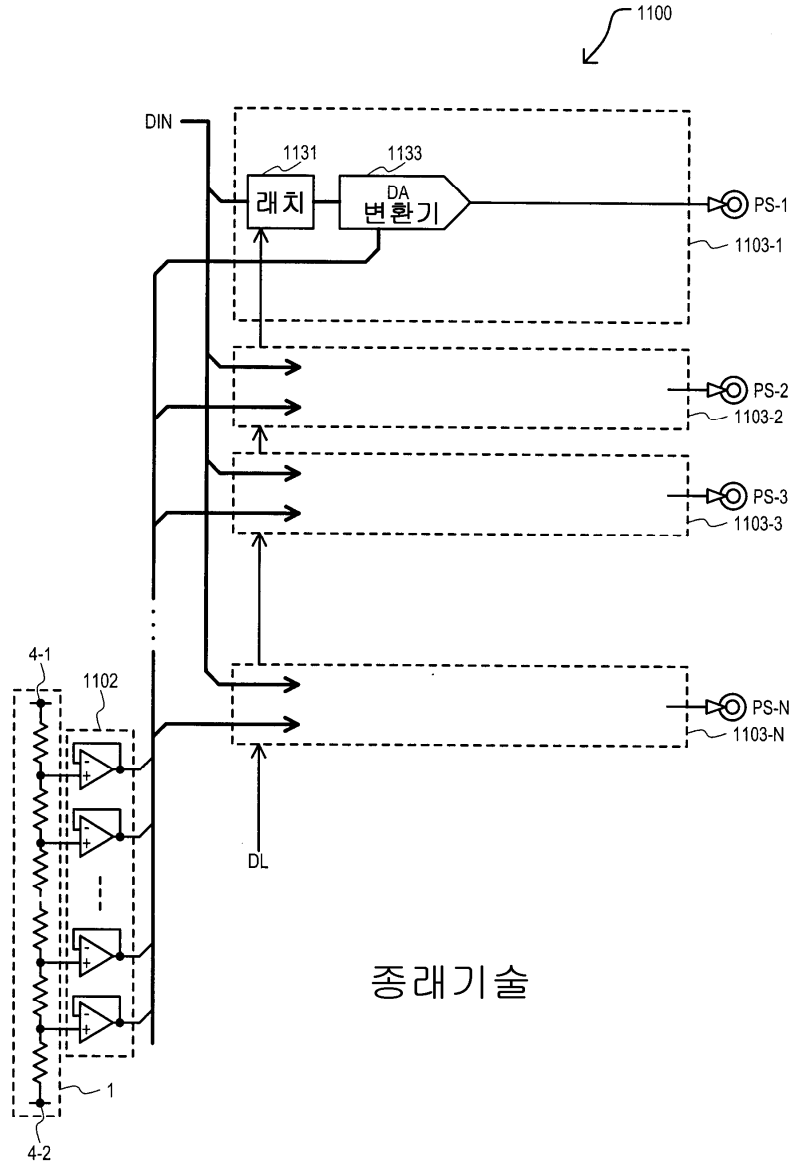


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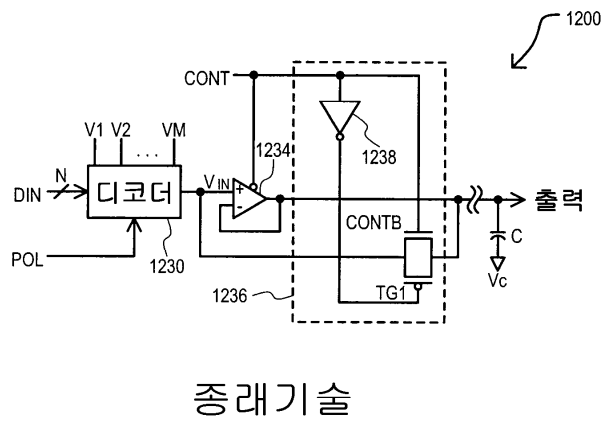




11



12



专利名称(译)	显示控制电路和显示装置		
公开(公告)号	KR1020030041787A	公开(公告)日	2003-05-27
申请号	KR1020020071522	申请日	2002-11-18
[标]申请(专利权)人(译)	瑞萨电子株式会社		
申请(专利权)人(译)	瑞萨电子株式会社		
[标]发明人	KATO FUMIHIKO 카토후미히코		
发明人	카토후미히코		
IPC分类号	G02F1/133 G09G3/20 G09G3/30 G09G3/32 G09G3/36		
CPC分类号	G09G3/3275 G09G3/3688 G09G3/3696 G09G2310/027 G09G2310/0291 G09G2330/021		
代理人(译)	用最甜		
优先权	2001353282 2001-11-19 JP		
其他公开文献	KR100569471B1		
外部链接	Espacenet		

摘要(译)

公开了一种具有降低的功耗的显示控制电路 (100)。显示控制电路100包括多个输出单元3-1至3-N。每个输出单元包括放大电路35，用于根据显示数据DIN将输出端子驱动到灰度级电压。放大电路35包括死区，当输出端基本上处于灰度电压时，该死区的输出是高阻抗。包括放大电路21以在灰度级电压附近为输出端子PS提供驱动。因此，通过放大电路35提供大的驱动和放大电路21的小驱动强度，降低了电流消耗。 1 指数方面 显示控制电路，显示控制装置

